

# SGH10N60RUFD

## Short Circuit Rated IGBT

### General Description

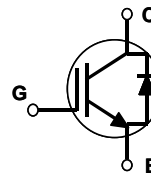
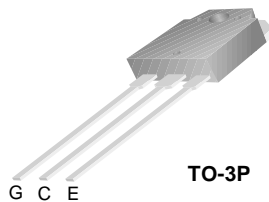
Fairchild's RUFD series of Insulated Gate Bipolar Transistors (IGBTs) provide low conduction and switching losses as well as short circuit ruggedness. The RUFD series is designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

### Features

- Short circuit rated 10us @  $T_C = 100^\circ\text{C}$ ,  $V_{GE} = 15\text{V}$
- High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.2\text{V}$  @  $I_C = 10\text{A}$
- High input impedance
- CO-PAK, IGBT with FRD :  $t_{rr} = 42\text{ns}$  (typ.)

### Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	SGH10N60RUFD	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C = 25^\circ\text{C}$	16	A
	Collector Current @ $T_C = 100^\circ\text{C}$	10	A
$I_{CM(1)}$	Pulsed Collector Current	30	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	12	A
$I_{FM}$	Diode Maximum Forward Current	92	A
$T_{SC}$	Short Circuit Withstand Time @ $T_C = 100^\circ\text{C}$	10	us
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	75	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	30	W
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction-to-Case	--	1.6	$^\circ\text{C/W}$
$R_{\theta JC}$ (DIODE)	Thermal Resistance, Junction-to-Case	--	2.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

**Electrical Characteristics of the IGBT**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\Delta BV_{CES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	$V/^\circ C$
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	$\mu A$
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	$\pm 100$	nA

**On Characteristics**

$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 10mA, V_{CE} = V_{GE}$	5.0	6.0	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 10A, V_{GE} = 15V$	--	2.2	2.8	V
		$I_C = 16A, V_{GE} = 15V$	--	2.5	--	V

**Dynamic Characteristics**

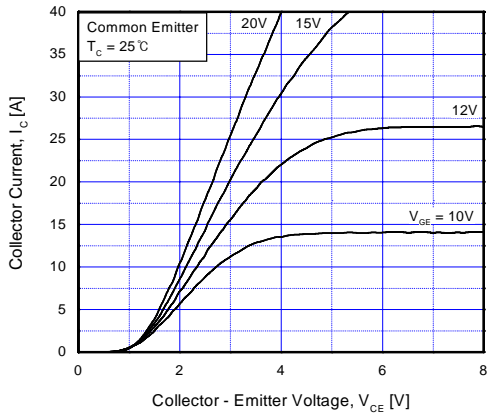
$C_{ies}$	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	--	660	--	pF
$C_{oes}$	Output Capacitance		--	115	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	25	--	pF

**Switching Characteristics**

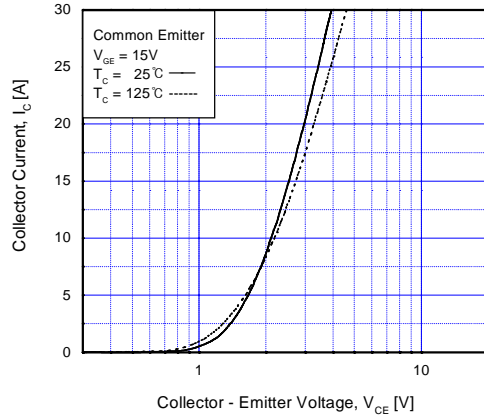
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 10A,$ $R_G = 20\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25^\circ C$	--	15	--	ns
$t_r$	Rise Time		--	30	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	36	50	ns
$t_f$	Fall Time		--	158	200	ns
$E_{on}$	Turn-On Switching Loss		--	141	--	$\mu J$
$E_{off}$	Turn-Off Switching Loss		--	215	--	$\mu J$
$E_{ts}$	Total Switching Loss	--	356	500	$\mu J$	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 10A,$ $R_G = 20\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 125^\circ C$	--	16	--	ns
$t_r$	Rise Time		--	33	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	42	60	ns
$t_f$	Fall Time		--	242	350	ns
$E_{on}$	Turn-On Switching Loss		--	161	--	$\mu J$
$E_{off}$	Turn-Off Switching Loss		--	452	--	$\mu J$
$E_{ts}$	Total Switching Loss	--	613	860	$\mu J$	
$T_{sc}$	Short Circuit Withstand Time	$V_{CC} = 300V, V_{GE} = 15V$ @ $T_C = 100^\circ C$	10	--	--	$\mu s$
$Q_g$	Total Gate Charge	$V_{CE} = 300V, I_C = 10A,$ $V_{GE} = 15V$	--	30	45	nC
$Q_{ge}$	Gate-Emitter Charge		--	5	10	nC
$Q_{gc}$	Gate-Collector Charge		--	8	16	nC
$L_e$	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

**Electrical Characteristics of DIODE**  $T_C = 25^\circ\text{C}$  unless otherwise noted

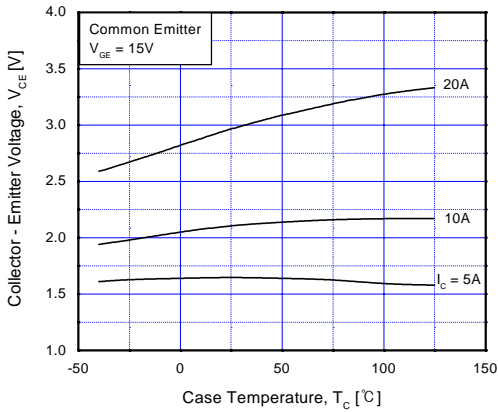
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
$V_{FM}$	Diode Forward Voltage	$I_F = 12A$	$T_C = 25^\circ C$	--	1.4	1.7	V
			$T_C = 100^\circ C$	--	1.3	--	
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 12A,$ $di/dt = 200A/\mu s$	$T_C = 25^\circ C$	--	42	60	ns
			$T_C = 100^\circ C$	--	60	--	
$I_{rr}$	Diode Peak Reverse Recovery Current	$I_F = 12A,$ $di/dt = 200A/\mu s$	$T_C = 25^\circ C$	--	3.5	6.0	A
			$T_C = 100^\circ C$	--	5.6	--	
$Q_{rr}$	Diode Reverse Recovery Charge	$I_F = 12A,$ $di/dt = 200A/\mu s$	$T_C = 25^\circ C$	--	80	180	nC
			$T_C = 100^\circ C$	--	220	--	



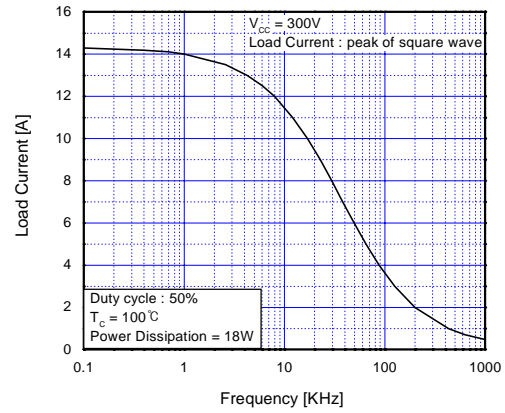
**Fig 1. Typical Output Characteristics**



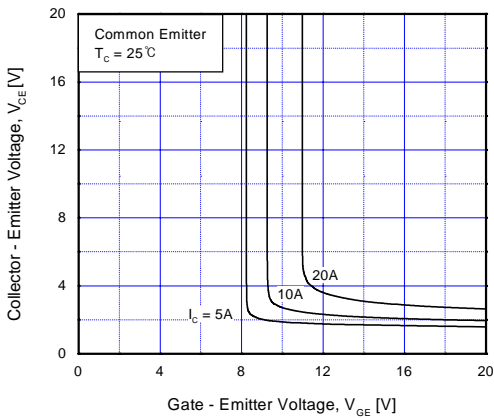
**Fig 2. Typical Saturation Voltage Characteristics**



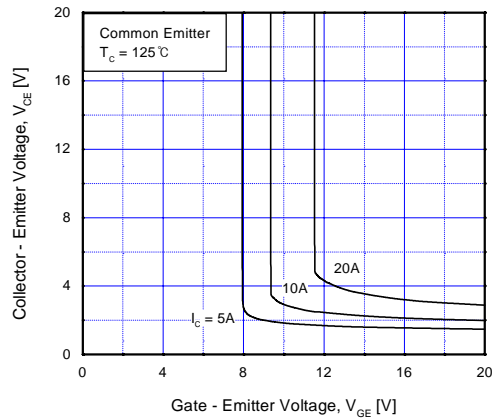
**Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level**



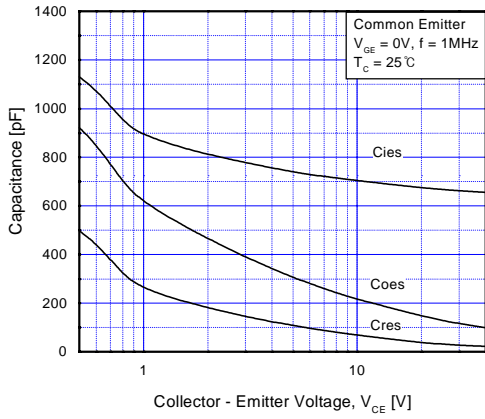
**Fig 4. Load Current vs. Frequency**



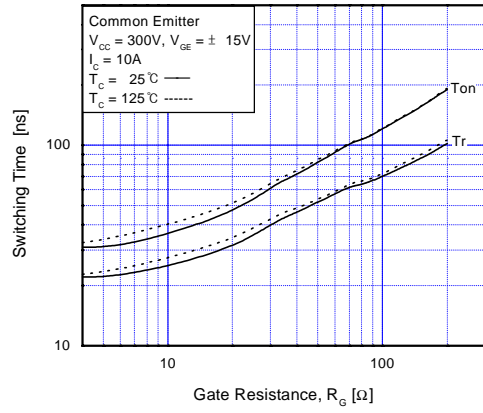
**Fig 5. Saturation Voltage vs.  $V_{GE}$**



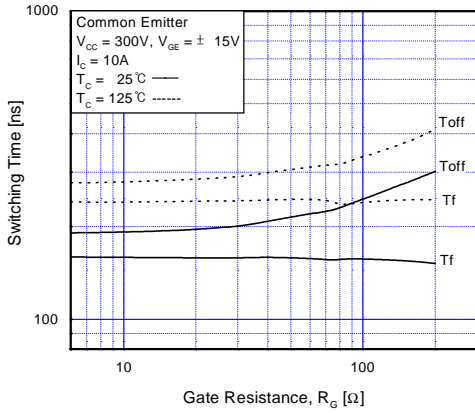
**Fig 6. Saturation Voltage vs.  $V_{GE}$**



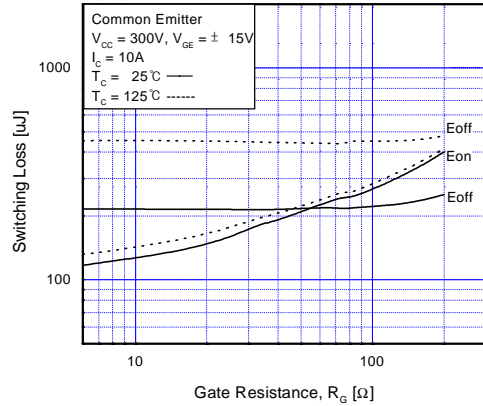
**Fig 7. Capacitance Characteristics**



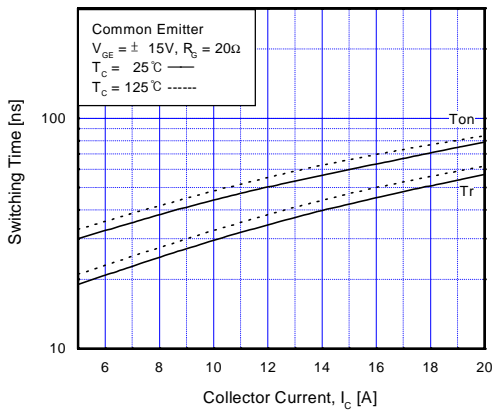
**Fig 8. Turn-On Characteristics vs. Gate Resistance**



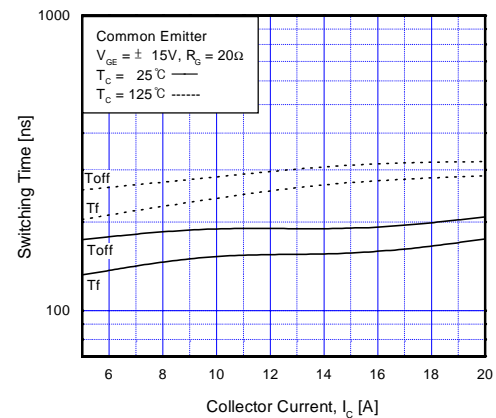
**Fig 9. Turn-Off Characteristics vs. Gate Resistance**



**Fig 10. Switching Loss vs. Gate Resistance**



**Fig 11. Turn-On Characteristics vs. Collector Current**



**Fig 12. Turn-Off Characteristics vs. Collector Current**

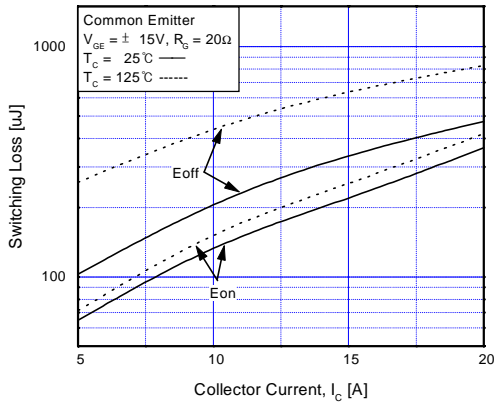


Fig 13. Switching Loss vs. Collector Current

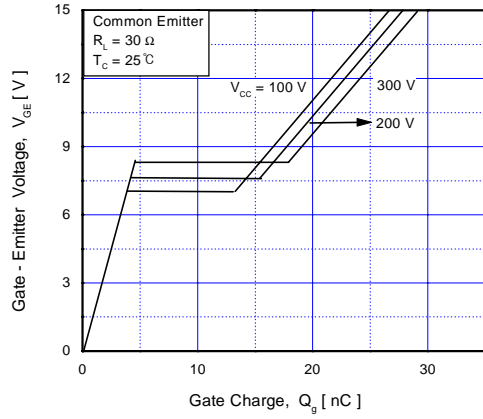


Fig 14. Gate Charge Characteristics

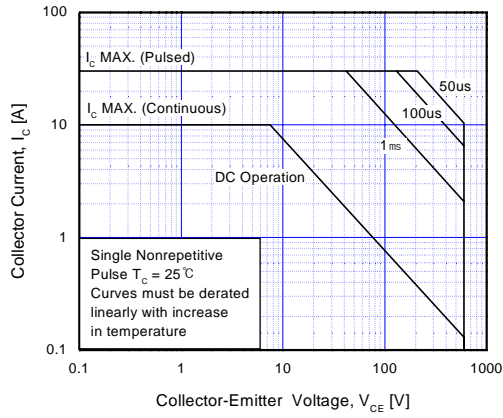


Fig 15. SOA Characteristics

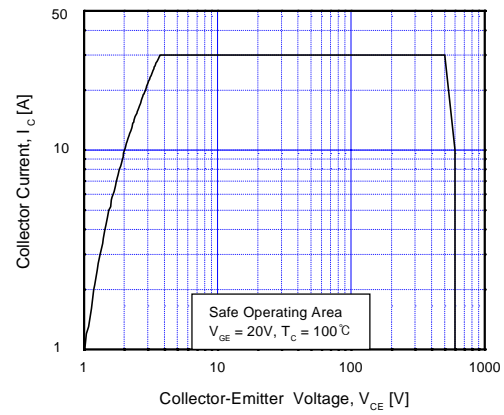


Fig 16. Turn-Off SOA Characteristics

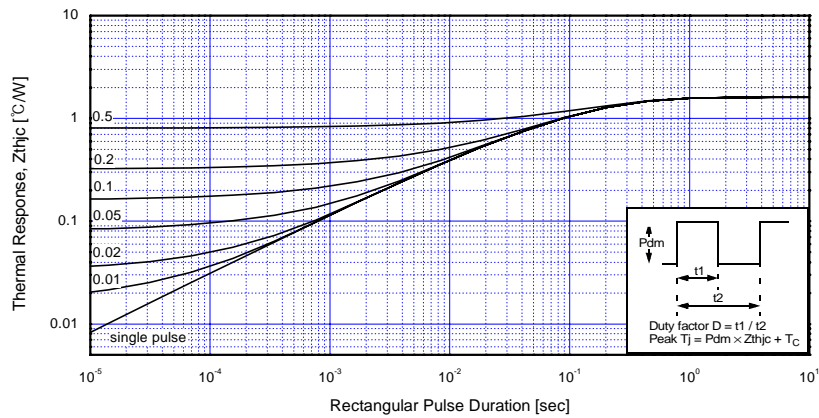


Fig 17. Transient Thermal Impedance of IGBT

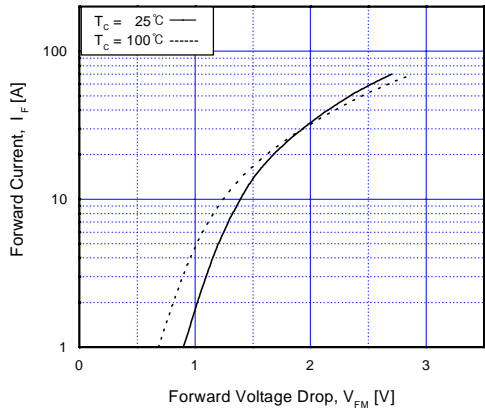


Fig 18. Forward Characteristics

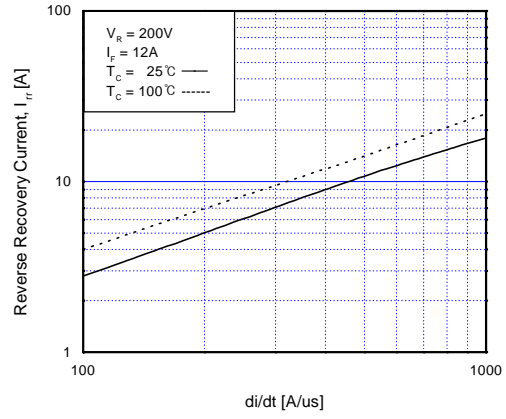


Fig 19. Reverse Recovery Current

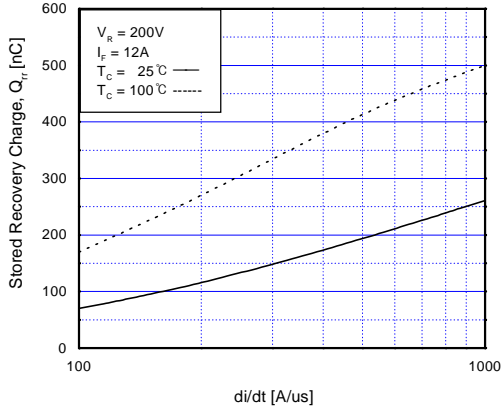


Fig 20. Stored Charge

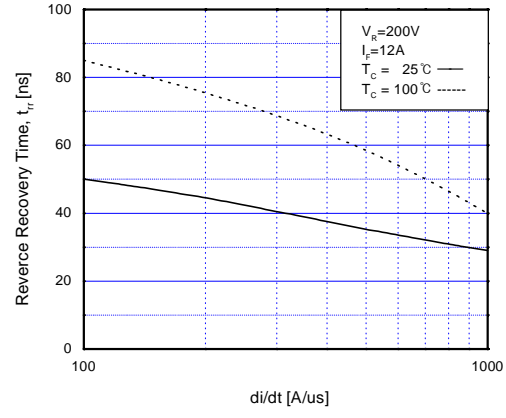
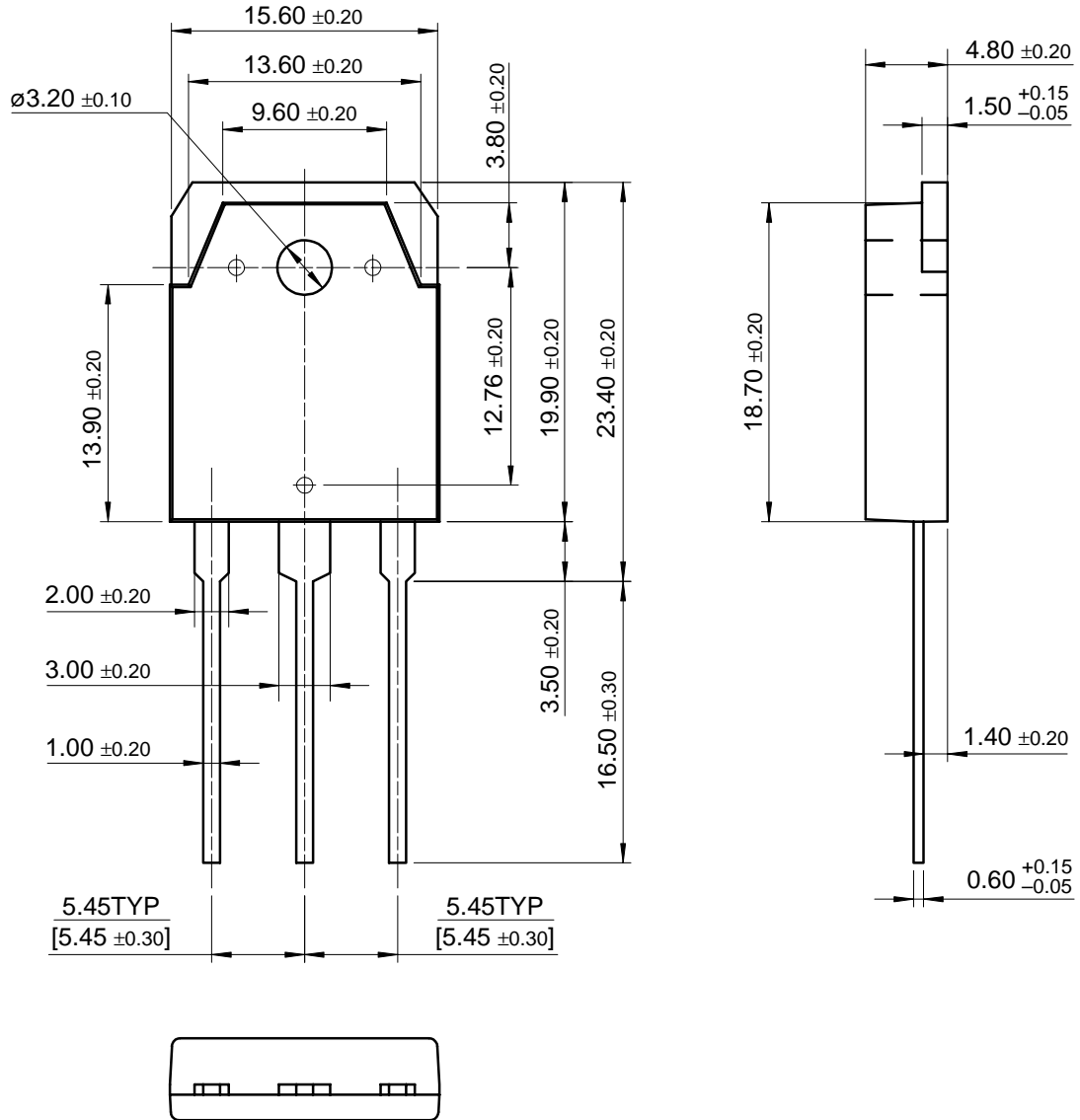


Fig 21. Reverse Recovery Time

Package Dimension

TO-3P



SGH10N60RUF D

Dimensions in Millimeters

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EcoSPARK™	I <sup>2</sup> C™	PowerTrench®	SuperSOT™-6	
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